

Shania Rehman

List of Publications by Year in descending order

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papers

503
citations

567281

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22
g-index

23
all docs

23
docs citations

23
times ranked

430
citing authors

#	ARTICLE	IF	CITATIONS
1	Thickness-dependent resistive switching in black phosphorus CBRAM. Journal of Materials Chemistry C, 2019, 7, 725-732.	5.5	51
2	Tunable resistive switching of vertical ReSe ₂ /graphene hetero-structure enabled by Schottky barrier height and DUV light. Journal of Alloys and Compounds, 2021, 855, 157310.	5.5	37
3	High mobility ReSe ₂ field effect transistors: Schottky-barrier-height-dependent photoresponsivity and broadband light detection with Co decoration. 2D Materials, 2020, 7, 015010.	4.4	36
4	Enhanced electrical and broad spectral (UV-Vis-NIR) photodetection in a Gr/ReSe ₂ /Gr heterojunction. Dalton Transactions, 2020, 49, 10017-10027.	3.3	36
5	Resistive Switching in Solution-Processed Copper Oxide (Cu _x O) by Stoichiometry Tuning. Journal of Physical Chemistry C, 2018, 122, 11076-11085.	3.1	34
6	Tuning of ionic mobility to improve the resistive switching behavior of Zn-doped CeO ₂ . Scientific Reports, 2019, 9, 19387.	3.3	28
7	Chemical Nature of Electrode and the Switching Response of RF-Sputtered NbO _x Films. Nanomaterials, 2020, 10, 2164.	4.1	28
8	Stable and Multilevel Data Storage Resistive Switching of Organic Bulk Heterojunction. Nanomaterials, 2021, 11, 359.	4.1	28
9	High performance complementary WS ₂ devices with hybrid Gr/Ni contacts. Nanoscale, 2020, 12, 21280-21290.	5.6	27
10	Optimization of ZnO:PEIE as an Electron Transport Layer for Flexible Organic Solar Cells. Energy & Fuels, 2021, 35, 12416-12424.	5.1	27
11	Neuro-Transistor Based on UV-Treated Charge Trapping in MoTe ₂ for Artificial Synaptic Features. Nanomaterials, 2020, 10, 2326.	4.1	26
12	Discrete memristive levels and logic gate applications of Nb ₂ O ₅ devices. Journal of Alloys and Compounds, 2021, 879, 160385.	5.5	22
13	Current Rectification, Resistive Switching, and Stable NDR Effect in BaTiO ₃ /CeO ₂ Heterostructure Devices. Advanced Electronic Materials, 2021, 7, 2001237.	5.1	19
14	Effect of oxygen stoichiometry on the threshold switching of RF-sputtered NbO _x (x=2.0-2.5) films. Materials Research Bulletin, 2021, 144, 111492.	5.2	18
15	Power efficient transistors with low subthreshold swing using abrupt switching devices. Nano Energy, 2022, 95, 107060.	16.0	16
16	Controlling the Wettability of ZnO Thin Films by Spray Pyrolysis for Photocatalytic Applications. Materials, 2022, 15, 3364.	2.9	16
17	Analog-digital hybrid computing with SnS ₂ memristor for low-powered sensor fusion. Nature Communications, 2022, 13, 2804.	12.8	14
18	Multi-heterostructured spin-valve junction of vertical FLG/MoSe ₂ /FLG. APL Materials, 2020, 8, .	5.1	11

#	ARTICLE	IF	CITATIONS
19	Development of directly grown "graphene" silicon Schottky barrier solar cell using co-doping technique. International Journal of Energy Research, 2022, 46, 11510-11522.	4.5	11
20	Flexible Diodes with Low Breakdown Voltage for Steep Slope Transistors and One Diode-One Resistor Applications. Advanced Electronic Materials, 2022, 8, .	5.1	8
21	Tunable Martensitic Transformation and Magnetic Properties of Sm-Doped NiMnSn Ferromagnetic Shape Memory Alloys. Crystals, 2021, 11, 1115.	2.2	5
22	Modulation of Magnetoresistance Polarity in BLG/SL-MoSe ₂ Heterostacks. Nanoscale Research Letters, 2020, 15, 136.	5.7	4
23	Optimization of SiO ₂ "TiO ₂ " nanocomposite in hole-transporting layer (PEDOT:PSS) for enhanced performance of planar Si-based hybrid solar cells. International Journal of Energy Research, 0, , .	4.5	1